Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.

Supporting information

Photo-response Modulation of Organic Transistors for Multi-level Light Sensing using Active Layer Microstructure Control

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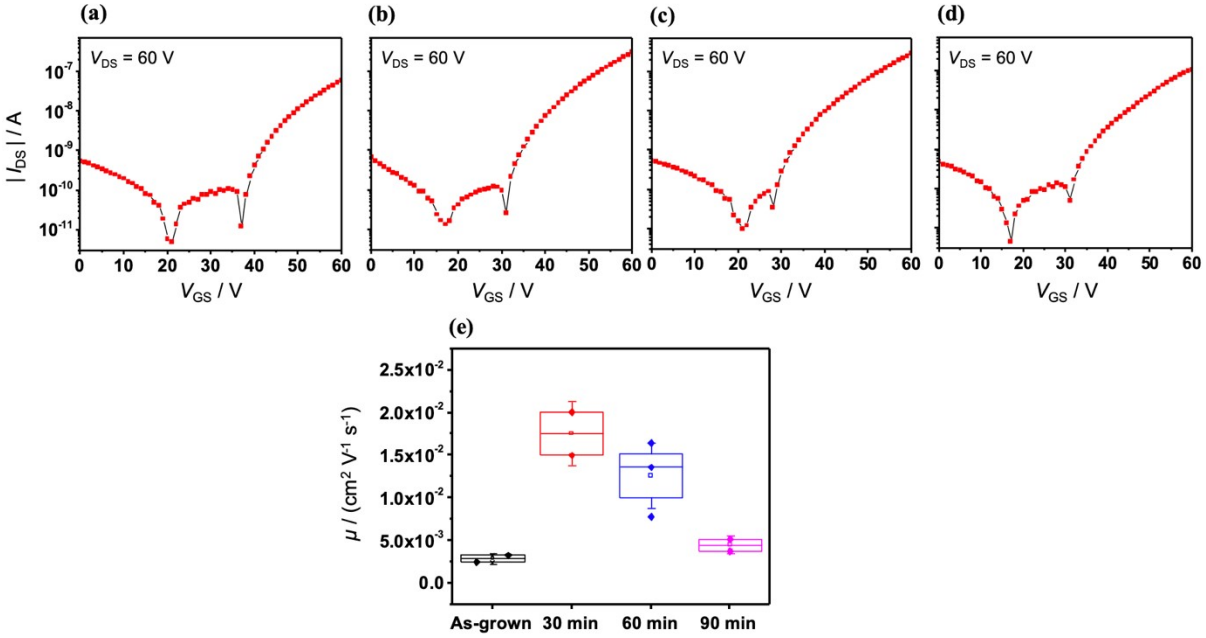

Figure S1. Transfer characteristics of devices with PTCDI-C_{13} films: (a) as-grown film, SVA treated (DCM vapor) film for (b) 30 min, (c) 60 min and (d) 90 min, and (e) measured field-effect mobilities of the devices.

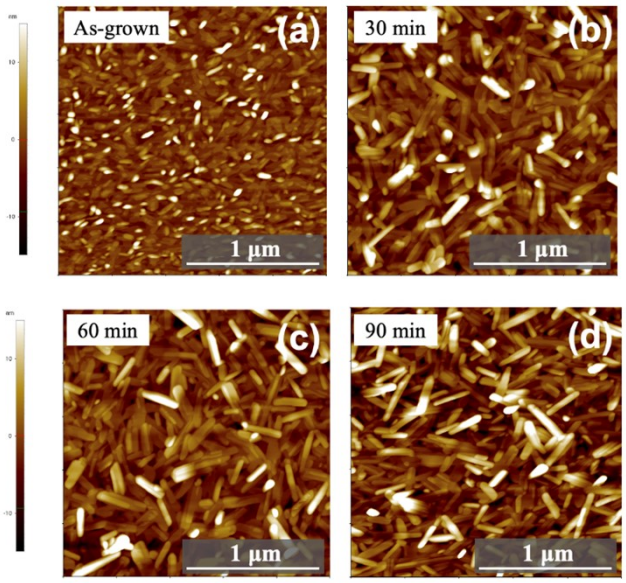

Figure S2. AFM images of PTCDI-C_{13} films: (a) as-grown film, SVA treated (DCM vapor) film for (b) 30 min, (c) 60 min, and (d) 90 min.

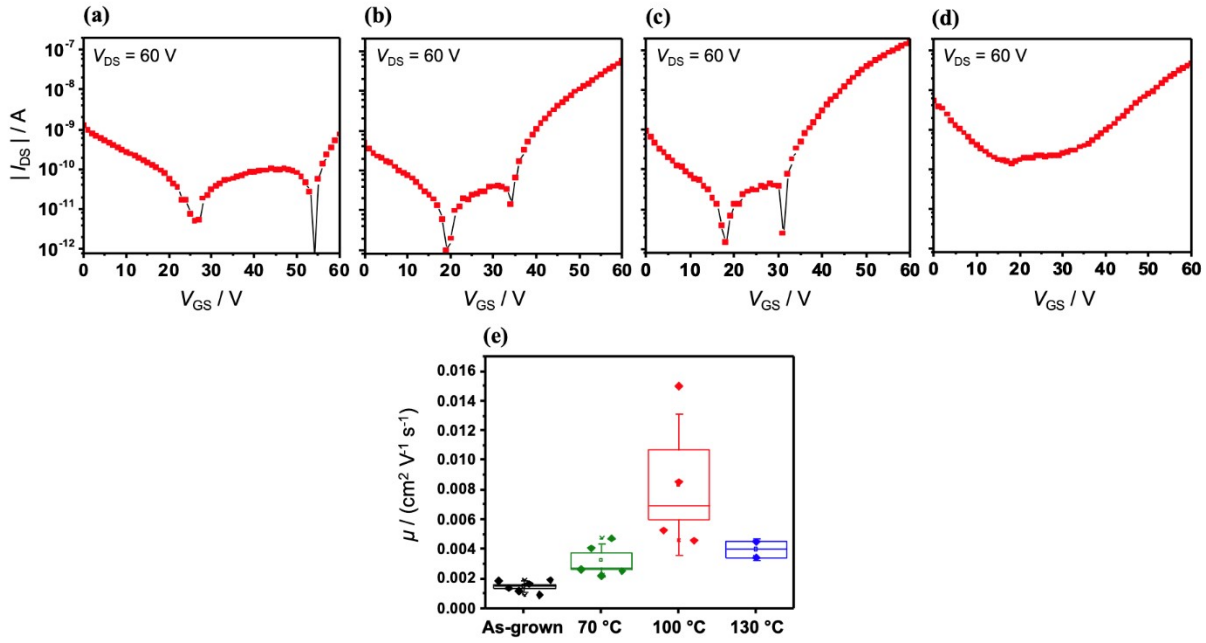

Figure S3. Transfer characteristics of devices with PTCDI-C_{13} films: (a) as-grown film, TA treated film at (b) 70 °C, (c) 100 °C, and (d) 130 °C for 15 min and, (e) measured field-effect mobilities of the devices.

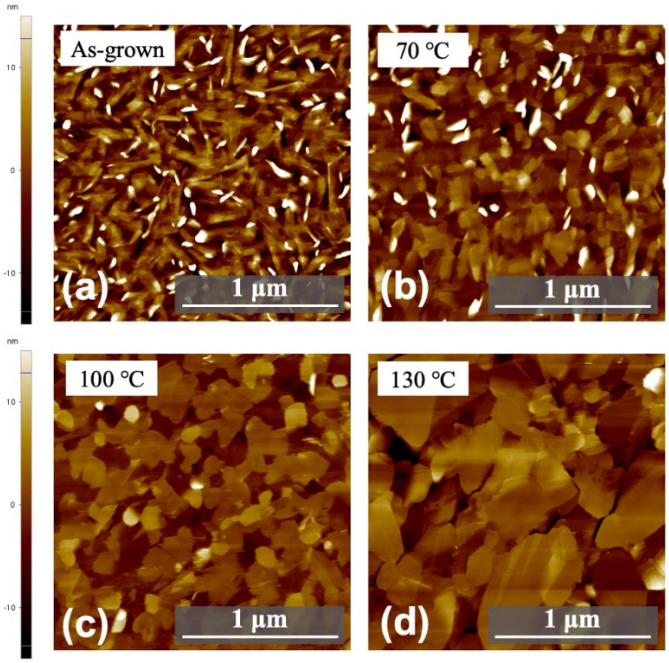

Figure S4. AFM images of PTCDI-C_{13} films: (a) as-grown film, TA treated film at (b) 70 °C, (c) 100 °C, and (d) 130 °C for 15 min.